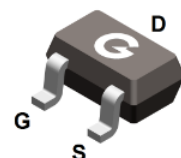
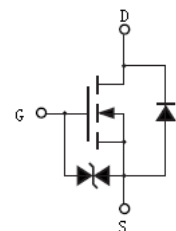


Features

- Fast switching speed
- HBM: AEC-Q101-001: H2 (JESD22-A114-B: 2)
- Halogen free
- Qualified to AEC-Q101 standards for high reliability

HF



SOT-323

Mechanical Data

- Case: SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBSS138BKW	SOT-323	3000 pcs / Tape & Reel	138BK

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_A = 25^\circ\text{C}$) *1	I_D	450	mA
Continuous Drain Current ($T_A = 70^\circ\text{C}$) *1		360	mA
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_A = 25^\circ\text{C}$)	I_{DM}	1800	mA
Power Dissipation ($T_A = 25^\circ\text{C}$) *1	P_D	300	mW
Operating Junction Temperature Range	T_J	$-55 \sim +150$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	-	420	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±10	μA
On Characteristics						
R _{DS(ON)}	Static Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 0.4A	-	0.56	0.7	Ω
		V _{GS} = 4.5V, I _D = 0.2A	-	0.64	1.2	
		V _{GS} = 2.5V, I _D = 0.1A	-	0.92	3	
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.8	1.0	1.5	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	42	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 30V f = 1.0MHz	-	65	-	pF
C _{OSS}	Output Capacitance		-	12	-	
C _{RSS}	Reverse Transfer Capacitance		-	7	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *3	V _{DD} = 30V V _{GS} = 10V I _D = 0.36A R _G = 6Ω	-	2	-	ns
t _r	Turn-on Rise Time *3		-	19	-	
t _{d(OFF)}	Turn-Off Delay Time *3		-	6	-	
t _f	Turn-Off Fall Time *3		-	23	-	
Q _G	Total Gate-Charge	V _{DS} = 30V V _{GS} = 4.5V I _D = 0.2A	-	2.3	-	nC
Q _{GS}	Gate to Source Charge		-	0.6	-	
Q _{GD}	Gate to Drain (Miller) Charge		-	0.5	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _S = 0.4A, V _{GS} = 0 V	-	0.8	1.4	V

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

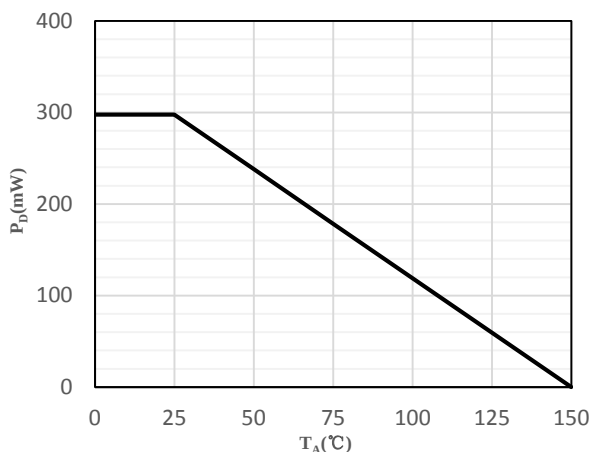


Fig 1 Power Dissipation

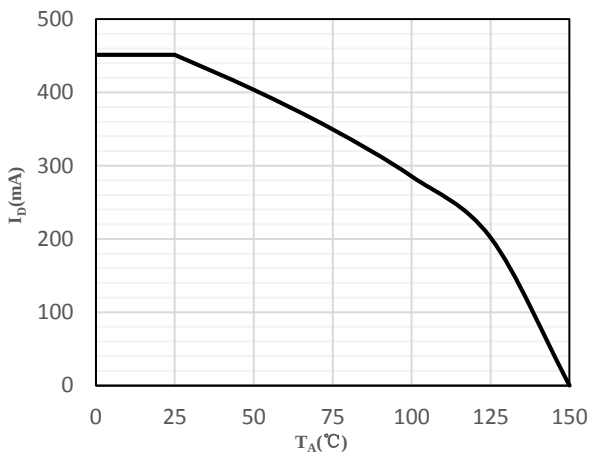


Fig 2 Drain Current

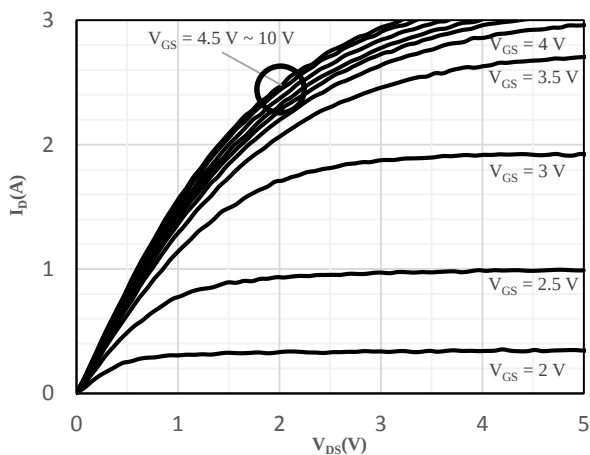


Fig 3 Typical Output Characteristics

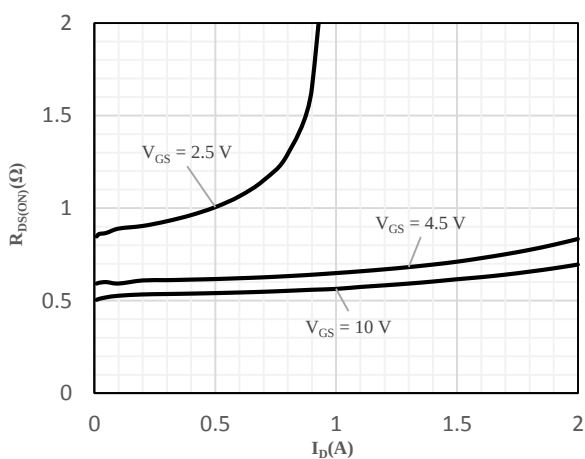


Fig 4 On-Resistance vs. Drain Current
and Gate Voltage

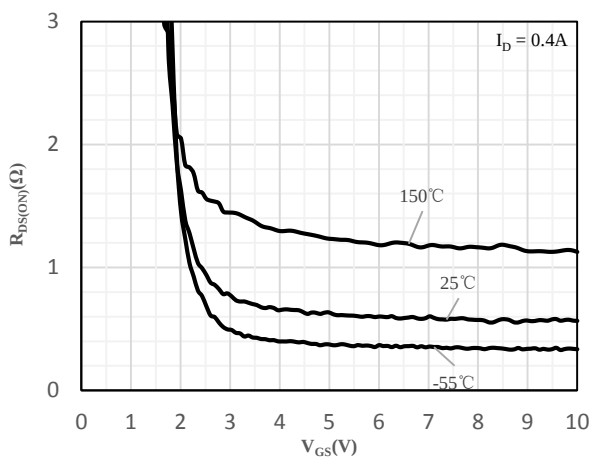


Fig 5 On-Resistance vs. Gate-Source Voltage

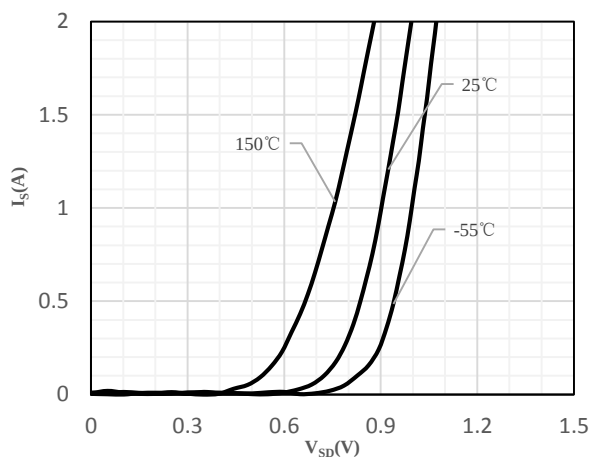


Fig 6 Body-Diode Characteristics

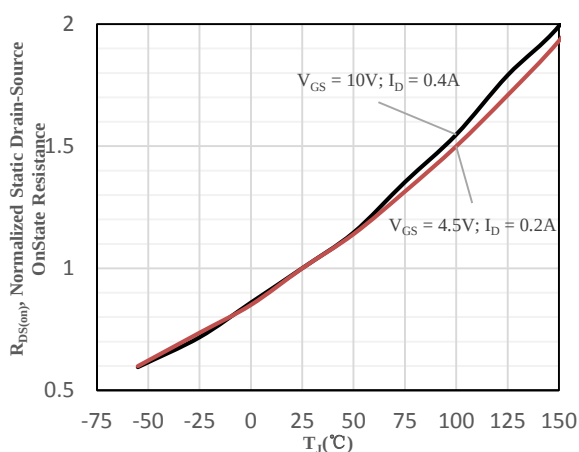


Fig 7 Normalized On-Resistance vs. Junction Temperature

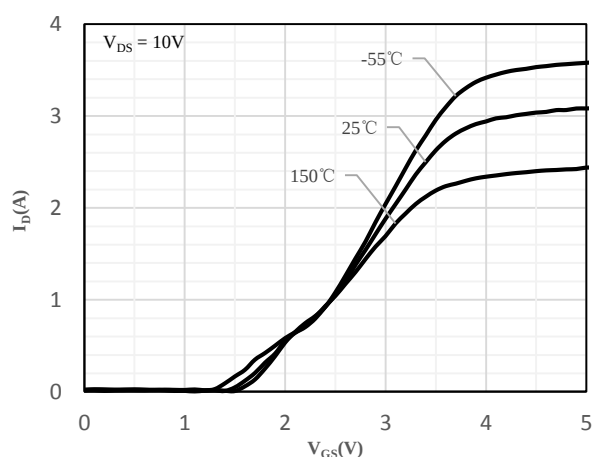


Fig 8 Transfer Characteristics

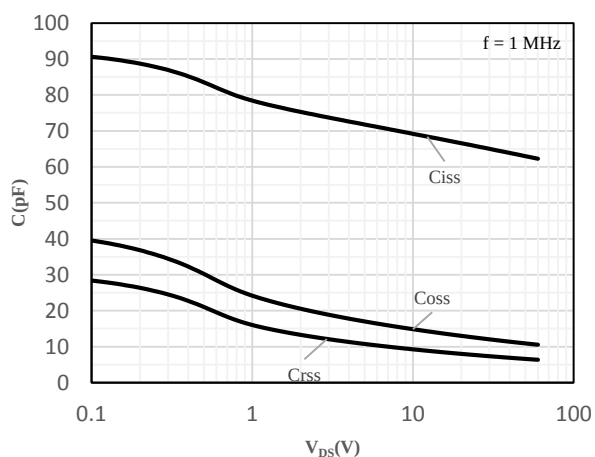


Fig 9 Capacitance Characteristics

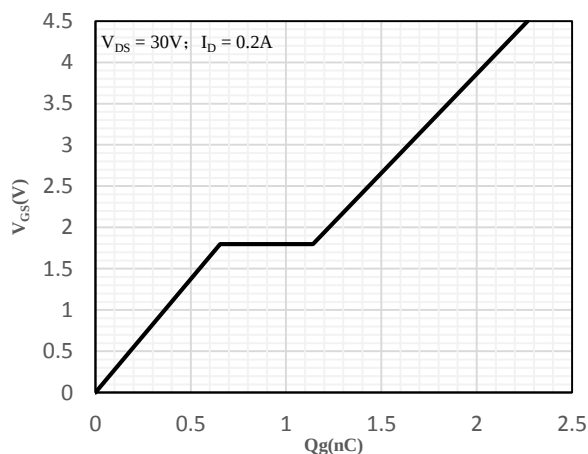


Fig 10 Gate-Charge Characteristics

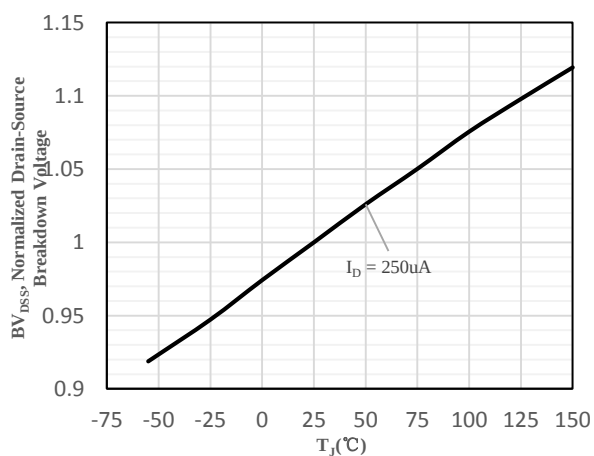


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

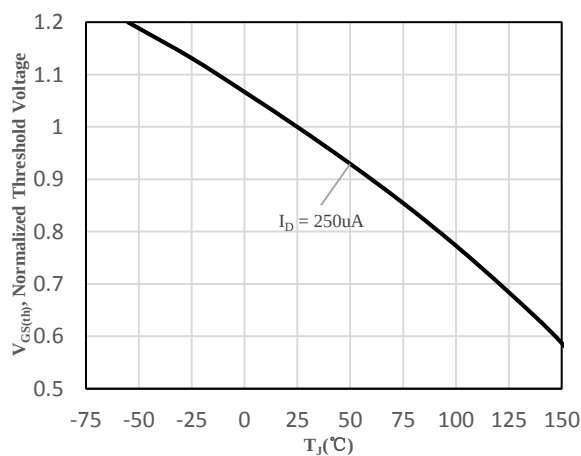
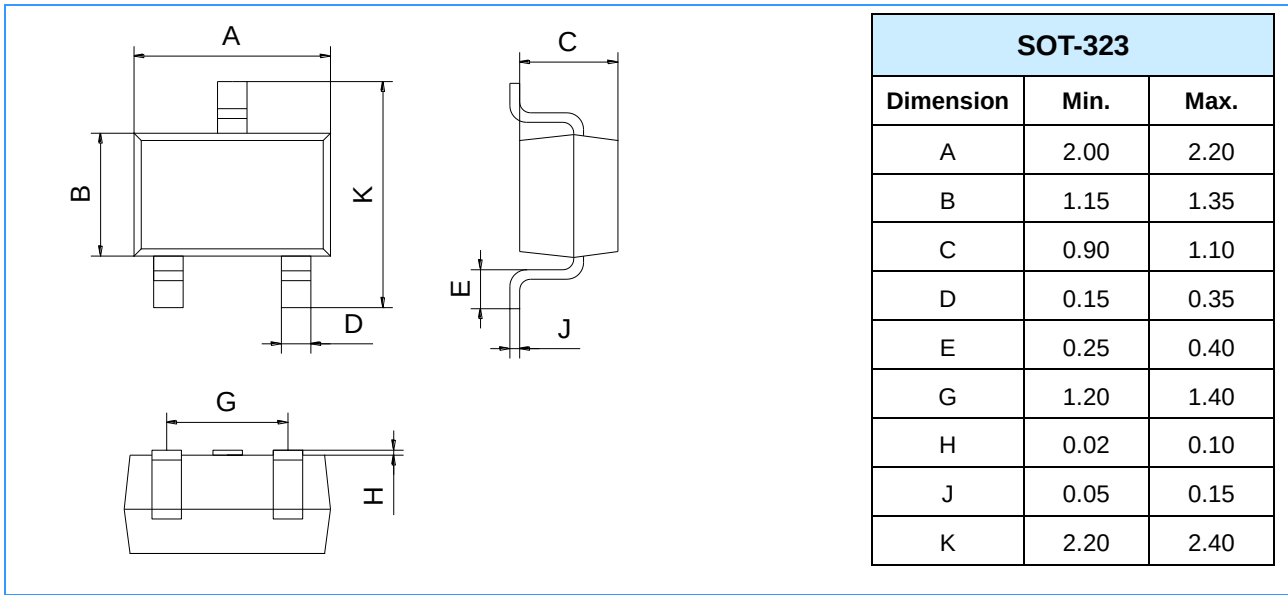
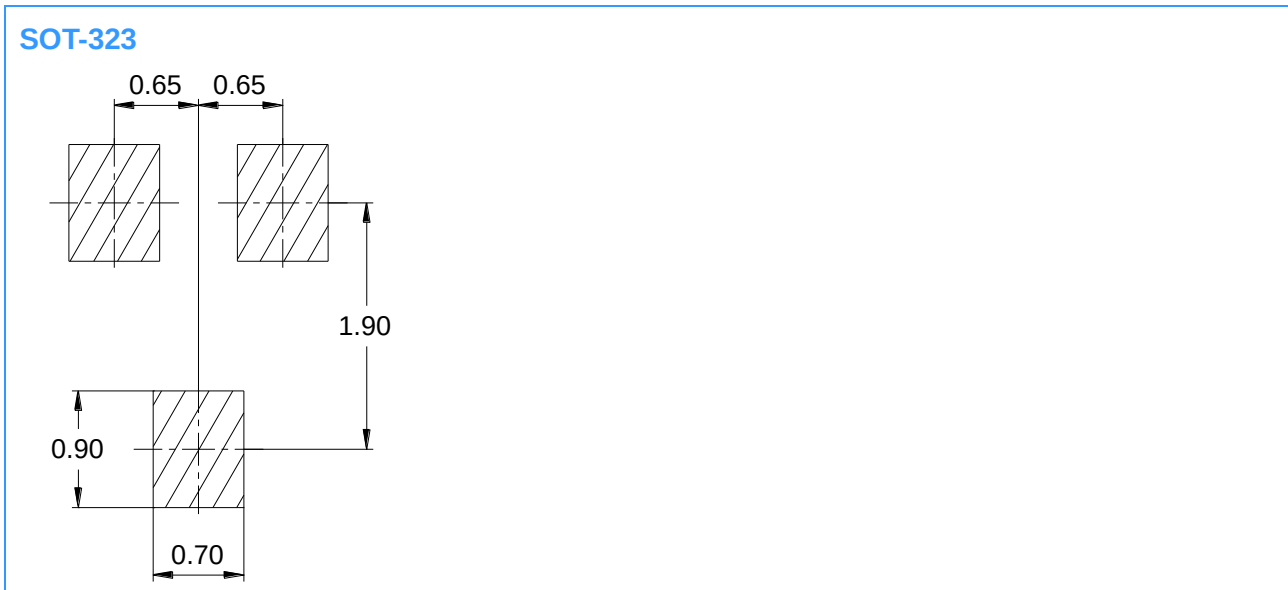


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



IMPORTANT NOTICE

Changzhou Galaxy Century Microelectronics (GME) reserves the right to make changes without further notice to any product information (copyrighted) herein to make corrections, modifications, improvements, or other changes. GME does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others.